AUK Semiconductor

SBC328

PNP Silicon Transistor

Descriptions

- High current application
- Switching application

Features

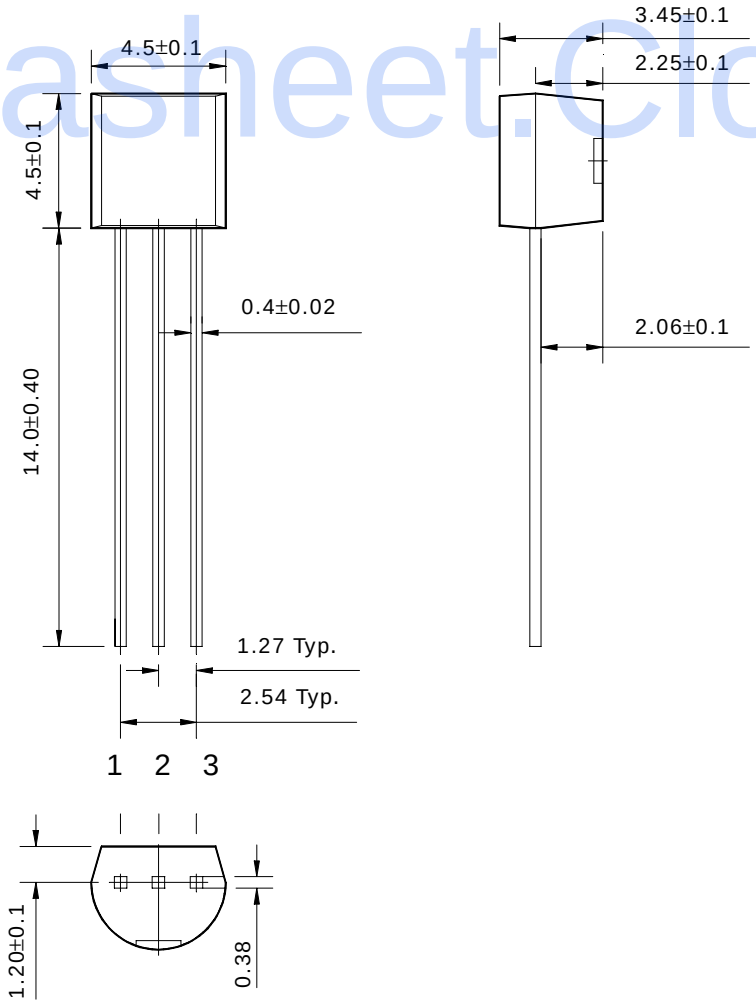
- Suitable for AF-Driver stage and low power output stages
- Complementary pair with SBC338

Ordering Information

Type NO.	Marking	Package Code
SBC328	SBC328	TO-92

Outline Dimensions

unit : mm



PIN Connections
1. Collector
2. Base
3. Emitter

Datasheet.Cloud

Absolute maximum ratings (Ta=25°C)

Characteristic	Symbol	Ratings	Unit
Collector-Base voltage	V_{CBO}	-30	V
Collector-Emitter voltage	V_{CEO}	-25	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-800	mA
Collector dissipation	P_C	625	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55~150	°C

Electrical Characteristics (Ta=25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Emitter breakdown voltage	BV_{CEO}	I_C=-1mA, I_B=0	-25	-	-	V
Base-Emitter Turn On voltage	$V_{BE(ON)}$	V_{CE}=-1V, I_C=-300mA	-	-	-1.2	V
Collector-Emitter saturation voltage	$V_{CE(sat)}$	I_C=-500mA, I_B=-50mA	-	-	-700	mV
Collector cut-off current	I_{CBO}	V_{CB}=-25V, I_E=0	-	-	-100	nA
DC current gain	h_{FE}*	V_{CE}=-1V, I_C=-100mA	100	-	630	-
Transition frequency	f_T	V_{CB}=-5V, I_E=10mA, f=100MHz	-	100	-	MHz
Collector output capacitance	Cob	V_{CB}=-10V, I_E=0, f=1MHz	-	16	-	pF

* : h_{FE} rank / 16(A) : 100 ~ 250, 25(B) : 160 ~ 400, 40(C) : 250 ~ 630

Electrical Characteristic Curves

Fig. 1 P_C-T_a

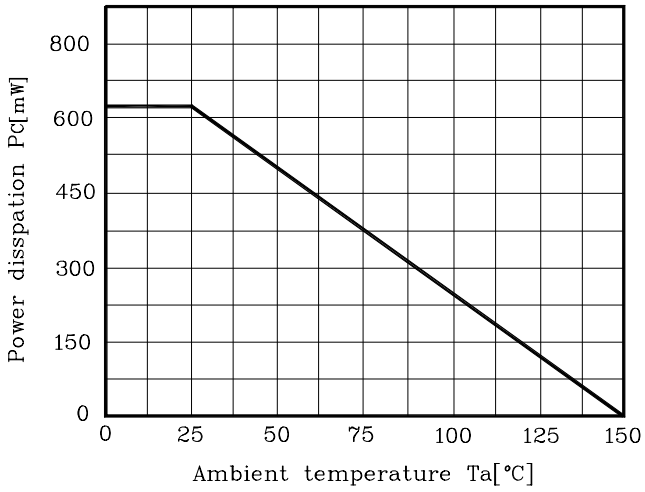


Fig. 2 IC -V_{BE}

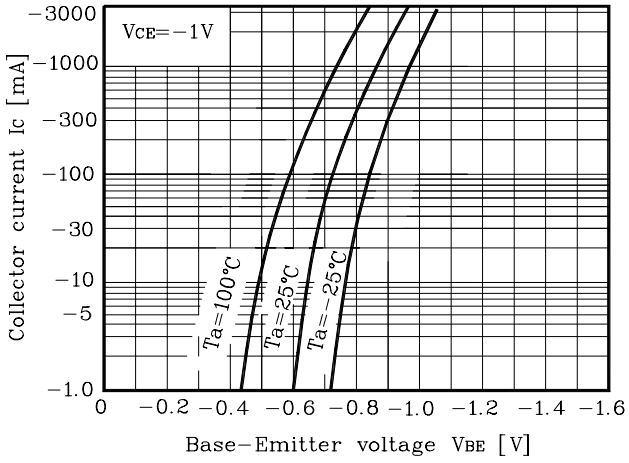


Fig. 3 I_C - V_{CE}

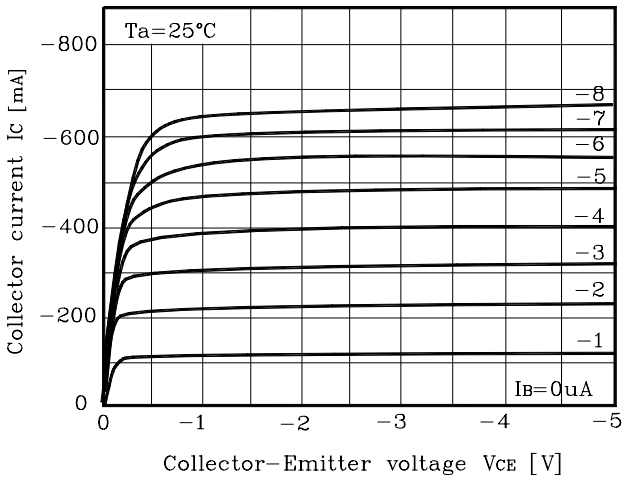


Fig. 4 h_{FE} - I_C

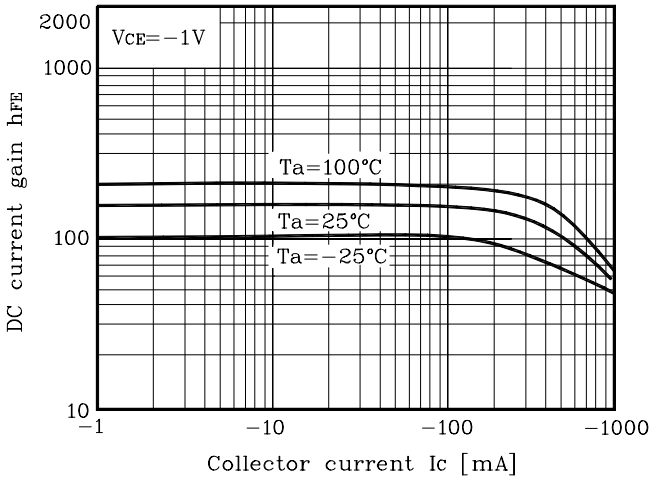
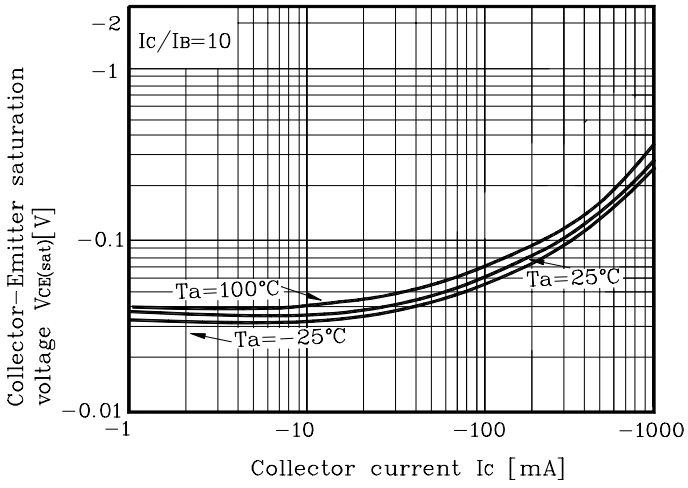



Fig. 5 $V_{CE(sat)}$ - I_C